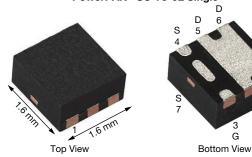


N-Channel 190 V (D-S) MOSFET

PowerPAK® SC-75-6L Single



Marking code: AC

PRODUCT SUMMARY									
V _{DS} (V)	190								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$	2.4								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 2.5 \text{ V}$	2.6								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 1.8 \text{ V}$	6								
Q _g typ. (nC)	2.3								
I _D (A) ^a	1.5								
Configuration	Single								

FEATURES

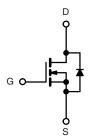
- TrenchFET® power MOSFET
- New thermally enhanced PowerPAK® SC-75 package
 - Small footprint area
 - Low on-resistance

FREE · Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

RoHS COMPLIANT HALOGEN

APPLICATIONS

• Boost converter for portable devices



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK SC-75
Lead (Pb)-free and halogen-free	SiB452DK-T1-GE3

ABSOLUTE MAXIMUM RATINGS	(T _A = 25 °C, unless	otherwise not	ed)			
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage		V_{DS}	190	V		
Gate-source voltage		V_{GS}	V _{GS} ± 16			
	T _C = 25 °C		1.5			
Continuous drain surrent /T 150 °C\	T _C = 70 °C	1 , [1.24			
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	l l _D	0.67 b, c			
	T _A = 70 °C		0.53 b, c	Α		
Pulsed drain current	•	I _{DM}	I _{DM} 1.5			
Out the second of the design of	T _C = 25 °C	,	1.5			
Continuous source-drain diode current	T _A = 25 °C	I _S	0.67 ^{b, c}			
	T _C = 25 °C		13			
Maximum naviar dissination	T _C = 70 °C		8.4	\Box w		
Maximum power dissipation	T _A = 25 °C	P _D	2.4 ^{b, c}	vv		
	T _A = 70 °C	1	1.6 ^{b, c}			
Operating junction and storage temperature rar	nge	T _J , T _{stg}	-55 to +150	°C		
Soldering recommendations (peak temperature	d, e		260			

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum junction-to-ambient b, f	t ≤ 5 s	R _{thJA}	41	51	°C/W				
Maximum junction-to-case (drain)	Steady state	R_{thJC}	7.5	9.5]				

Notes

- a. $T_C = 25$ °C
- b. Surface mounted on 1" x 1" FR4 board
- t = 5 s
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

 Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 105 °C/W



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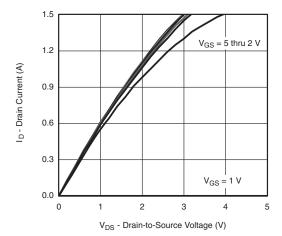
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	V _{GS} = 0 V, I _D = 250 μA	190	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	J 250 A	-	202	-	m)//°C
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-3.2	-	mV/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.6	-	1.5	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 16 \text{ V}$	-	-	± 100	nA
Zero gate voltage drain current	1	$V_{DS} = 190 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	
zero gate voltage drain current	I _{DSS}	$V_{DS} = 190 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55 ^{\circ}\text{C}$	-	-	10	μA
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	1.5	-	-	Α
		$V_{GS} = 4.5 \text{ V}, I_D = 0.5 \text{ A}$	-	1.8	2.4	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 2.5 V, I _D = 0.45 A	-	1.9	2.6	Ω
		$V_{GS} = 1.8 \text{ V}, I_D = 0.2 \text{ A}$	-	2	6	
Forward transconductance a	9fs	V _{DS} = 10 V, I _D = 0.5 A	-	3	-	S
Dynamic ^b						
Input capacitance	C _{iss}		=	135	-	
Output capacitance	Coss	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	9	-	рF
Reverse transfer capacitance	C _{rss}		-	6	-	
Tatal asta shauna	0	$V_{DS} = 95 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 0.7 \text{ A}$	-	4.3	6.5	nC
Total gate charge	Q _g		-	2.3	3.5	
Gate-source charge	Q _{gs}	$V_{DS} = 95 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 0.7 \text{ A}$	-	0.4	-	
Gate-drain charge	Q _{gd}		-	1	-	
Gate resistance	R _g	f = 1 MHz	-	2.2	-	Ω
Turn-on delay time	t _{d(on)}		-	12	20	
Rise time	t _r	$V_{DD} = 95 \text{ V}, R_L = 190 \Omega$	-	16	25	
Turn-off delay time	t _{d(off)}	$I_D\cong 0.5~A,~V_{GEN}=4.5~V,~R_g=1~\Omega$	-	30	45	
Fall time	t _f		-	15	25	
Turn-on delay time	t _{d(on)}		-	5	10	ns
Rise time	t _r	$V_{DD} = 95 \text{ V}, R_L = 190 \Omega$	-	10	15	
Turn-off delay time	t _{d(off)}	$I_D\cong 0.5$ A, $V_{GEN}=10$ V, $R_g=1~\Omega$	-	10	15	_
Fall time	t _f		-	10	15	
Drain-Source Body Diode Characterist	ics					
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	1.5	Λ.
Pulse diode forward current	I _{SM}		-	-	1.5	Α
Body diode voltage	V_{SD}	$I_S = 0.5 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.8	1.2	V
Body diode reverse recovery time	t _{rr}		-	40	60	ns
Body diode reverse recovery charge	Q _{rr}	$I_F = 0.5 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	-	45	70	nC
Reverse recovery fall time	t _a	T _J = 25 °C	-	20	-	
Reverse recovery rise time	t _b		-	19	_	ns

Notes

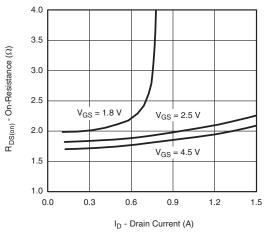
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

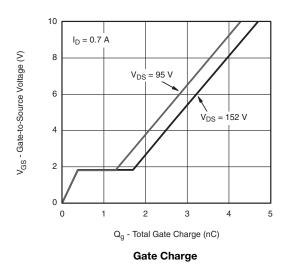


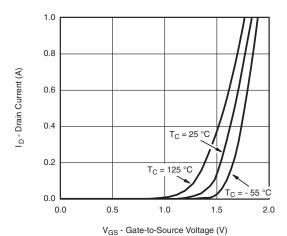


Output Characteristics

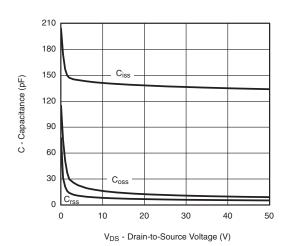


On-Resistance vs. Drain Current and Gate Voltage

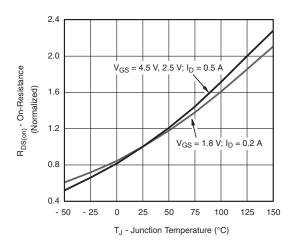




Transfer Characteristics

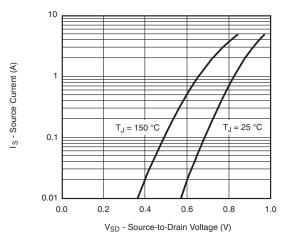


Capacitance

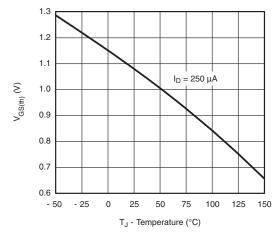


On-Resistance vs. Junction Temperature

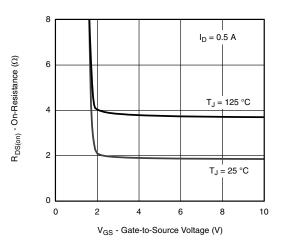




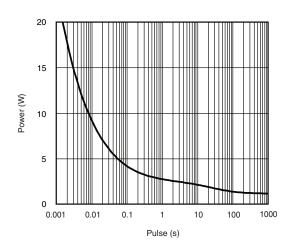
Source-Drain Diode Forward Voltage



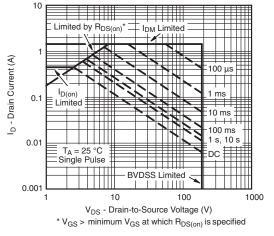
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

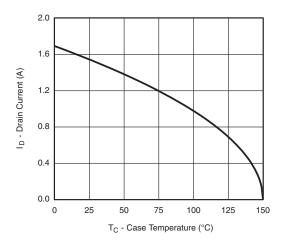


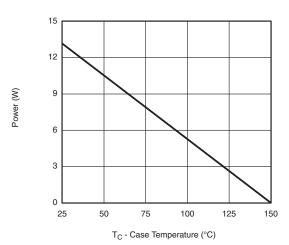
Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient







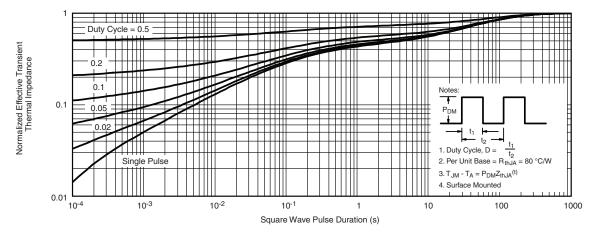
Current Derating a

Power Derating

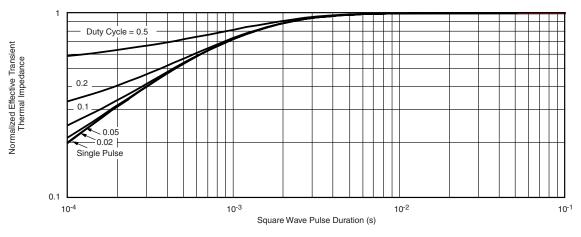
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



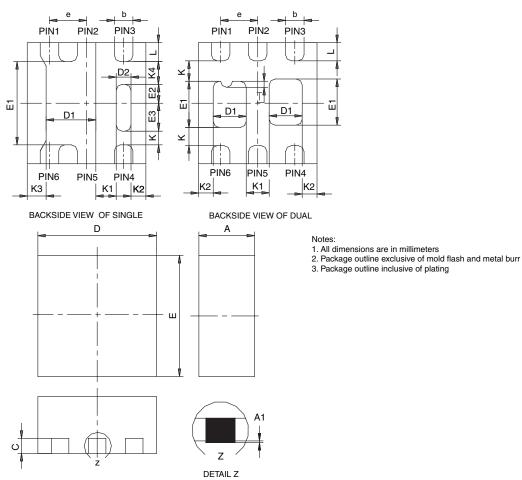
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?68832.





PowerPAK® SC75-6L



	SINGLE PAD						DUAL PAD					
DIM	M	ILLIMETE	RS		INCHES		M	MILLIMETERS			INCHES	
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021
D2	0.10	0.20	0.30	0.004	0.008	0.012						
Е	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028
E2	0.20	0.25	0.30	0.008	0.010	0.012						
E3	0.32	0.37	0.42	0.013	0.015	0.017						
е		0.50 BSC			0.020 BSC	;	0.50 BSC 0.020 BSC					
K		0.180 TYP)		0.007 TYP		0.245 TYP			0.010 TYP		
K1		0.275 TYP	1	0.011 TYP			0.320 TYP			0.013 TYP		
K2		0.200 TYP 0.008 TYP			0.200 BSC			0.008 TYP				
K3		0.255 TYP 0.010 TYP				•						
K4	0.300 TYP 0.012 TYP											
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014
T							0.03	0.08	0.13	0.001	0.003	0.005

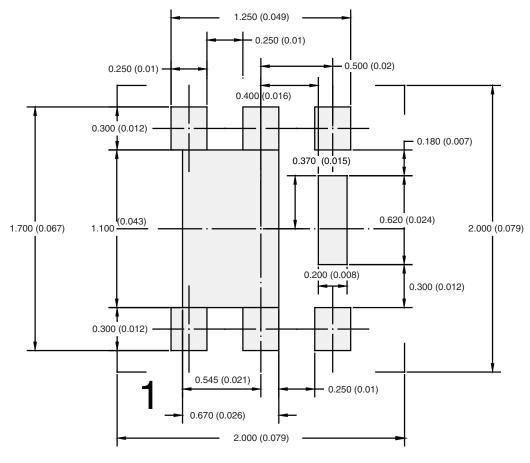
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DWG: 5935

Document Number: 73000 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC75-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT



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